

10/077784

COP/C
AP

PTO/SB/17 (12-04v2)

Approved for use through 7/31/2006. OMB 0651-0032

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no person are required to respond to a collection of information unless it displays a valid OMB control number.

Effective on 12/08/2004.

Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818).

FEE TRANSMITTAL

For FY 2005

 Applicant claims small entity status. See 37 CFR 1.27

TOTAL AMOUNT OF PAYMENT (\$ 100.00)
Complete if Known

Application Number	Patent#: 6,847,535 B2
Filing Date	Issued: January 25, 2005
First Named Inventor	Terry L. Gilton
Examiner Name	T. Q. Phan
Art Unit	2818
Attorney Docket No.	M4065.0482/P482

METHOD OF PAYMENT (check all that apply)

<input type="checkbox"/> Check	<input checked="" type="checkbox"/> Credit Card	<input type="checkbox"/> Money Order	<input type="checkbox"/> None	<input type="checkbox"/> Other (please identify): _____
<input checked="" type="checkbox"/> Deposit Account Deposit Account Number: 04-1073 Deposit Account Name: Dickstein Shapiro Morin & Oshinsky LLP				

For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)

<input type="checkbox"/> Charge fee(s) indicated below	<input type="checkbox"/> Charge fee(s) indicated below, except for the filing fee
<input type="checkbox"/> Charge any additional fee(s) or underpayment of fee(s) under 37 CFR 1.16 and 1.17	<input checked="" type="checkbox"/> Credit any overpayments

FEE CALCULATION**1. BASIC FILING, SEARCH, AND EXAMINATION FEES**

<u>Application Type</u>	<u>FILING FEES</u>		<u>SEARCH FEES</u>		<u>EXAMINATION FEES</u>		
	<u>Fee (\$)</u>	<u>Small Entity</u>	<u>Fee (\$)</u>	<u>Small Entity</u>	<u>Fee (\$)</u>	<u>Small Entity</u>	<u>Fees Paid (\$)</u>
Utility	300	150	500	250	200	100	
Design	200	100	100	50	130	65	
Plant	200	100	300	150	160	80	
Reissue	300	150	500	250	600	300	
Provisional	200	100	0	0	0	0	

2. EXCESS CLAIM FEESFee Description

Each claim over 20 (including Reissues)

<u>Small Entity</u>	
<u>Fee (\$)</u>	<u>Fee (\$)</u>

50 25

Each independent claim over 3 (including Reissues)

200 100

Multiple dependent claims

360 180

<u>Total Claims</u>	<u>Extra Claims</u>	<u>Fee (\$)</u>	<u>Fee Paid (\$)</u>
- =	x	=	

<u>Multiple Dependent Claims</u>	
<u>Fee (\$)</u>	<u>Fee Paid (\$)</u>

<u>Indep. Claims</u>	<u>Extra Claims</u>	<u>Fee (\$)</u>	<u>Fee Paid (\$)</u>
- =	x	=	

3. APPLICATION SIZE FEE

If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).

<u>Total Sheets</u>	<u>Extra Sheets</u>	<u>Number of each additional 50 or fraction thereof</u>	<u>Fee (\$)</u>	<u>Fee Paid (\$)</u>
- 100 =	/50	(round up to a whole number) x	=	

4. OTHER FEE(S)

Non-English Specification, \$130 fee (no small entity discount)

Other (e.g., late filing surcharge): 1811 Certificate of correction

100.00

SUBMITTED BY

Signature		Registration No. (Attorney/Agent)	28,371	Telephone	(202) 828-2232
Name (Print/Type)	Thomas J. D'Amico			Date	December 28, 2005

Certificate

JAN 03 2006

of Correction

JAN 05 2006



Docket No.: M4065.0482/P482
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
Terry L. Gilton et al.

Patent No.: 6,847,535 *B2*

Issued: January 25, 2005

For: REMOVABLE PROGRAMMABLE
CONDUCTOR MEMORY CARD AND
ASSOCIATED READ/WRITE DEVICE AND
METHOD OF OPERATION

REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 C.F.R. §§ 1.322 & 1.323

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted an omission and several typographical errors which should be corrected.

In the Specification, the USPTO made the following errors:

Column 4, line 49, "card illustrated" **should read** --card 200 inserted within the housing 302 define the location of the memory cells 202 illustrated--; **and**

Column 5, line 44, "which is has" **should read** --which has--;

12/29/2005 SZEWDIE1 00000058 6847535
01 FC:1811 100.00 DP

DSMDB.1997368.1

JAN 05 2006

In the Specification, Applicants made the following error:

Column 4, line 47, "At shown" should read --As shown--.

In the Claims, the USPTO made the following error:

Claim 27, column 9, line 4, "at cast" should read --at least--.

In the Claims, Applicants made the following error:

Claim 27, column 9, line 6, "at lest" should read --at least--.

In the Other Publications portion of References Cited, the PTO made the following errors:

"Alekperova, Sh.M.; Gadzhleva, G.S., Current-Voltage characteristics of Ag₂Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139."

Should read:

--Alekperova, Sh.M.; Gadzhleva, G.S., Current-Voltage characteristics of Ag₂Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.--;

"Elliot, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034."

Should read:

--Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.--;

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relation in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985."

Should read:

--Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relation in fast ion and mixed conductors, Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985.—; and

"Welrauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73."

Should read:

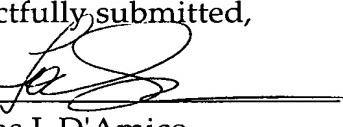
--Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73.--.

The errors were both found in the application as filed by applicants and made by the USPTO. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed. The errors now sought to be corrected are inadvertent typographical errors the correction of which does not involve new matter or require reexamination. Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentee respectfully solicits the granting of the requested Certificate of Correction.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0482/P482.

Dated: December 28, 2005

Respectfully submitted,

By 
Thomas J. D'Amico

Registration No.: 28,371

Ryan H. Flax

Registration No.: 48,141

DICKSTEIN SHAPIRO MORIN &
OSHINSKY LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorneys for Applicants

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**Page 1 of 2

PATENT NO. : 6,847,535 B2
APPLICATION NO. : 10/077,784
ISSUE DATE : January 25, 2005
INVENTOR(S) : Terry L. Gilton et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Specification, the following errors are corrected:

Column 4, line 47, "At shown" should read --As shown--;

Column 4, line 49, "card illustrated" should read --card 200 inserted within the housing 302 define the location of the memory cells 202 illustrated--; and

Column 5, line 45, "which is has" should read --which has--.

In the Claims, the following errors are corrected:

Claim 27, Column 9, line 4, "at cast" should read --at least--; and

Claim 27, column 9, line 6, "at lest" should read --at least--.

In the Other Publications portion of References Cited, the following errors are corrected:

"Alekperova, Sh.M.; Gadzhleva, G.S., Current-Voltage characteristics of Ag₂Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139."

Should read:

--Alekperova, Sh.M.; Gadzhleva, G.S., Current-Voltage characteristics of Ag₂Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.--;

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 1
2101 L Street NW
Washington, DC 20037-1526

DSMDB.1997366.1

JAN 05 2006

"Elliot, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034."

Should read:

--Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.--;

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relation in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985."

Should read:

--Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relation in fast ion and mixed conductors, Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985.—; and

"Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73."

Should read:

--Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73.--.

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 2
2101 L Street NW
Washington, DC 20037-1526

DSMDB.1997366.1

JAN 05 2006